

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2921)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

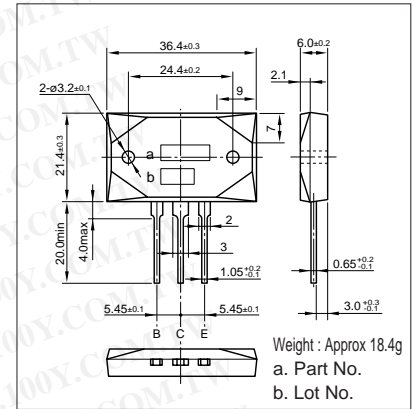
Symbol	Ratings	Unit
V _{CB0}	-160	V
V _{CEO}	-160	V
V _{EBO}	-5	V
I _C	-15	A
I _B	-4	A
P _C	150(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =-160V	-100max	μA
I _{EBO}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _C =-25mA	-160min	V
h _{FE}	V _{CE} =-4V, I _C =-5A	50min*	
V _{CE(sat)}	I _C =-5A, I _B =-0.5A	-2.0max	V
f _r	V _{CE} =-12V, I _E =2A	50typ	MHz
COB	V _{CB} =-10V, f=1MHz	400typ	pF

*h_{FE} Rank O(50 to 100), P(70 to 140), Y(90 to 180)

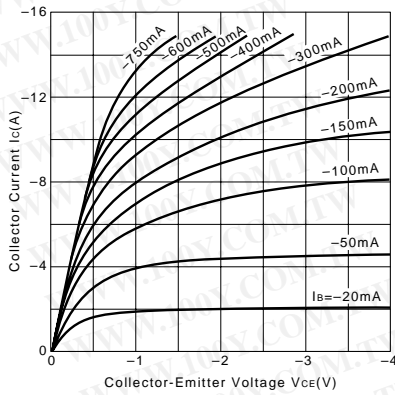
External Dimensions MT-200



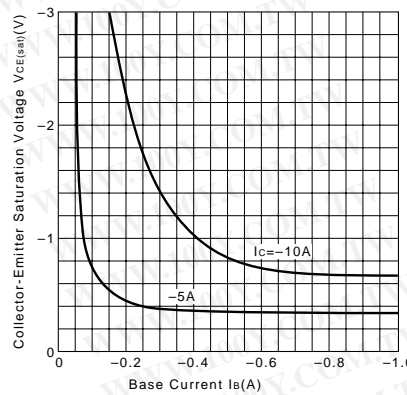
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{B2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-60	12	-5	5	-500	500	0.25typ	0.85typ	0.2typ

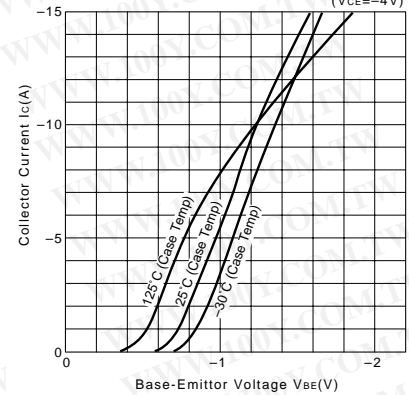
I_C-V_{CE} Characteristics (Typical)



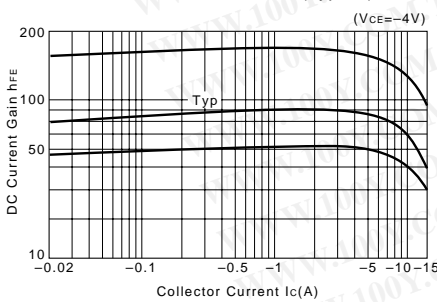
V_{CE(sat)}-I_B Characteristics (Typical)



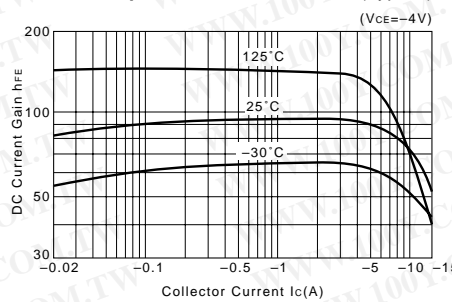
I_C-V_{BE} Temperature Characteristics (Typical)



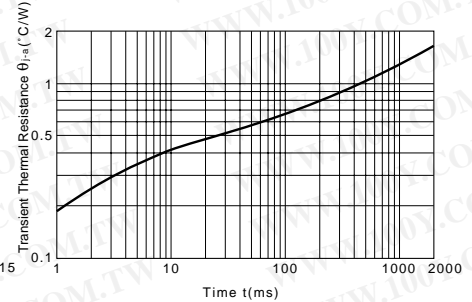
h_{FE}-I_C Characteristics (Typical)



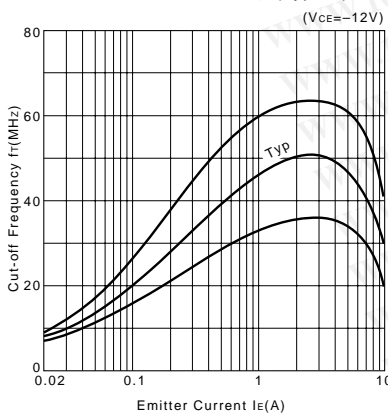
h_{FE}-I_C Temperature Characteristics (Typical)



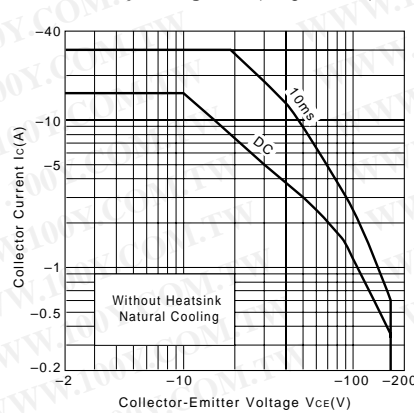
θ_{j-a}-t Characteristics



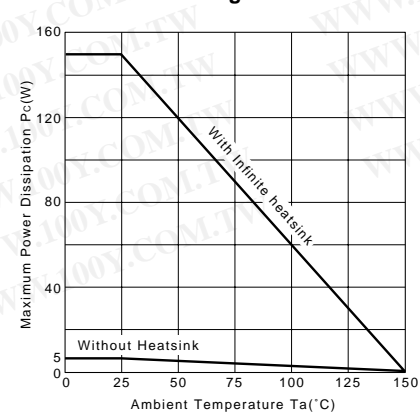
f_r-I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C-T_a Derating



Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1215)

Application : Audio and General Purpose

■Absolute maximum ratings (Ta=25°C)

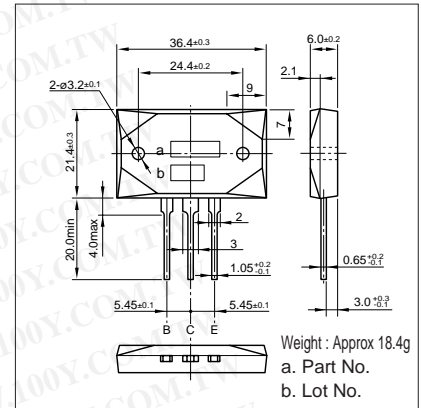
Symbol	Ratings	Unit
V _{CB0}	160	V
V _{CE0}	160	V
V _{EB0}	5	V
I _C	15	A
I _B	4	A
P _C	150(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =160V	100max	μA
I _{EB0}	V _{EB} =5V	100max	μA
V(BR)CEO	I _C =25mA	160min	V
h _{FE}	V _{CE} =4V, I _C =5A	50min*	
V _{CE(sat)}	I _C =5A, I _B =0.5A	2.0max	V
f _r	V _{CE} =12V, I _E =-2A	60typ	MHz
COB	V _{CB} =10V, f=1MHz	200typ	pF

*h_{FE} Rank: O(50 to 100), P(70 to 140), Y(90 to 180)

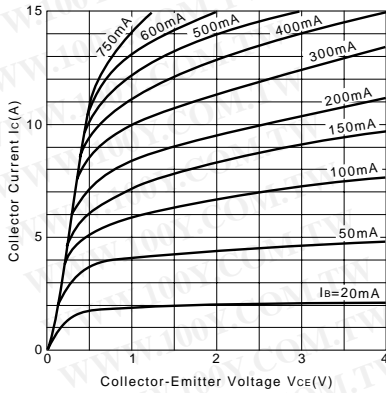
External Dimensions MT-200



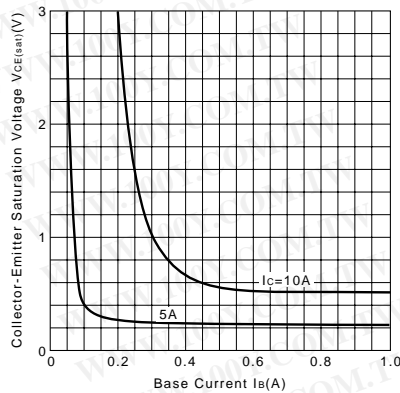
■Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{B2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
60	12	5	-5	500	-500	0.2typ	1.5typ	0.35typ

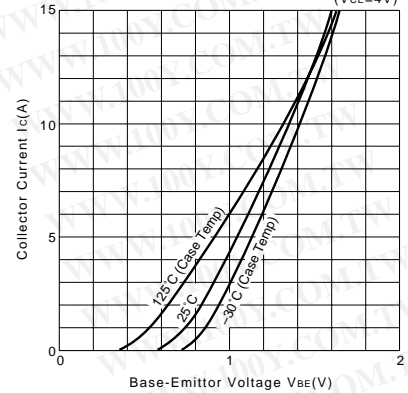
I_C-V_{CE} Characteristics (Typical)



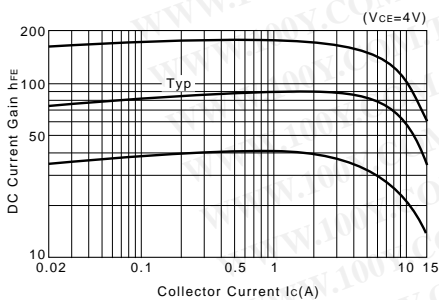
V_{CE(sat)}-I_B Characteristics (Typical)



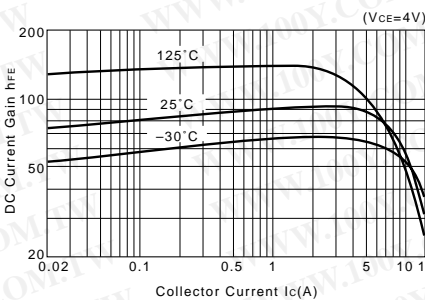
I_C-V_{BE} Temperature Characteristics (Typical)



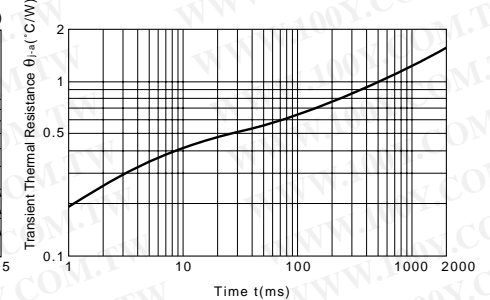
h_{FE}-I_C Characteristics (Typical)



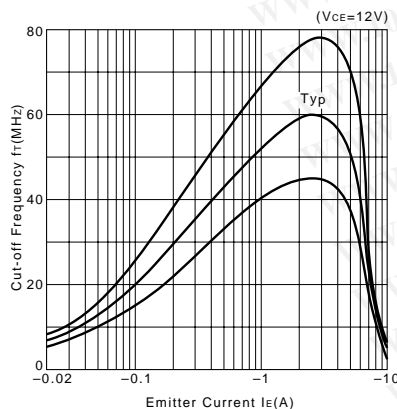
h_{FE}-I_C Temperature Characteristics (Typical)



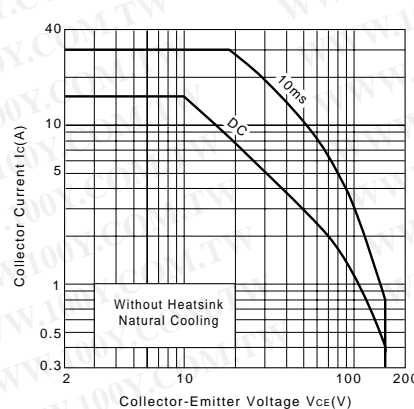
θ_{J-a}-t Characteristics



f_r-I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C-T_a Derating

